implanting a first pocket implant into the semiconductor substrate from a first side of the gate; and

implanting a second pocket implant into the semiconductor substrate from a second side of the gate, wherein the first pocket implant is approximately in contact with the second pocket implant.

28. (Amended) The method of claim 27 further comprising diffusing the first pocket implant and the second pocket implant laterally in the semiconductor substrate.

35. (Amended) A method of fabricating a transistor in an integrated circuit device comprising:

providing a semiconductor substrate;

forming a gate oxide on the semiconductor substrate;

forming a gate on the gate oxide;

implanting a first pocket implant and a second pocket implant into the semiconductor substrate using the gate as a mask; and

diffusing the first and second pocket implants laterally causing the first pocket implant to merge with the second pocket implant.

36. (Amended) The method of claim 35 wherein the diffusing increases a reverse short channel effect of the transistor.

37. (Amended) The method of claim 35 further comprising implanting an enhancement implant in the semiconductor substrate.

38. (New) A method of fabricating a transistor in an integrated circuit device comprising:

providing a semiconductor substrate;

forming a gate oxide on the semiconductor substrate;

forming a gate on the gate oxide;

implanting a first pocket implant into the semiconductor substrate from a first side of the gate at an angle; and

implanting a second pocket implant into the semiconductor substrate from a second side of the gate at an angle;

wherein the concentration of pocket implant under the gate is nonuniform.

39. (New) The method of claim 38 further comprising diffusing the first pocket implant and the second pocket implant laterally in the semiconductor substrate.

40. (New) The method of claim 38 wherein the first pocket implant and the second pocket implant are implanted using the gate as a mask.